

SANYO

No.2923

2SC4413

NPN Epitaxial Planar Silicon Transistor

Low-Frequency
General-Purpose Amp Applications**Features**

- Very small-sized package permitting the 2SC4413-applied sets to be made small and slim
- Adoption of FBET process
- High DC current gain
- Low collector to emitter saturation voltage
- High V_{EBO}
- Small c_{ob}

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

			unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	50	V
Emitter to Base Voltage	V_{EBO}	15	V
Collector Current	I_C	100	mA
Collector Current(Pulse)	I_{CP}	200	mA
Base Current	I_B	20	mA
Collector Dissipation	P_C	150	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

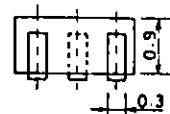
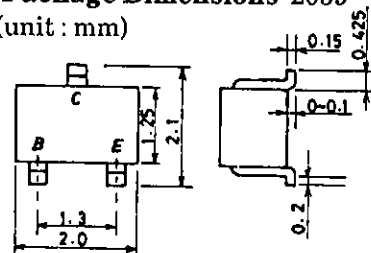
Electrical Characteristics at $T_a = 25^\circ\text{C}$

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 40\text{V}, I_E = 0$			0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 10\text{V}, I_C = 0$			0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = 5\text{V}, I_C = 10\text{mA}$	800	1500	3200	
Gain-Bandwidth Product	f_T	$V_{CE} = 10\text{V}, I_C = 10\text{mA}$		200		MHz
Output Capacitance	c_{ob}	$V_{CB} = 10\text{V}, f = 1\text{MHz}$		1.5		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 50\text{mA}, I_B = 1\text{mA}$		0.1	0.5	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = 50\text{mA}, I_B = 1\text{mA}$		0.8	1.1	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10\mu\text{A}, I_E = 0$	60			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}, R_{BE} = \infty$	50			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu\text{A}, I_C = 0$	15			V

Marking : GY

Package Dimensions 2059

(unit : mm)

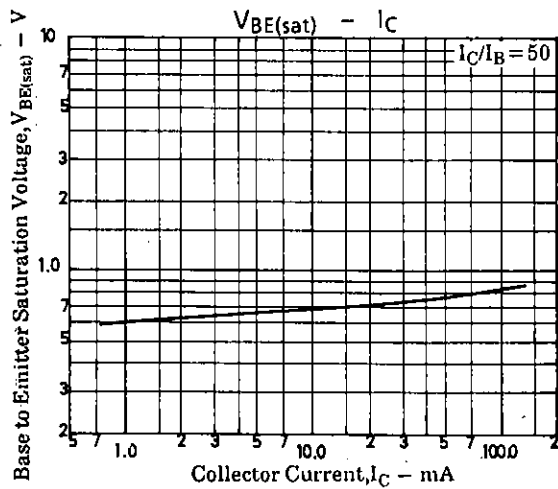
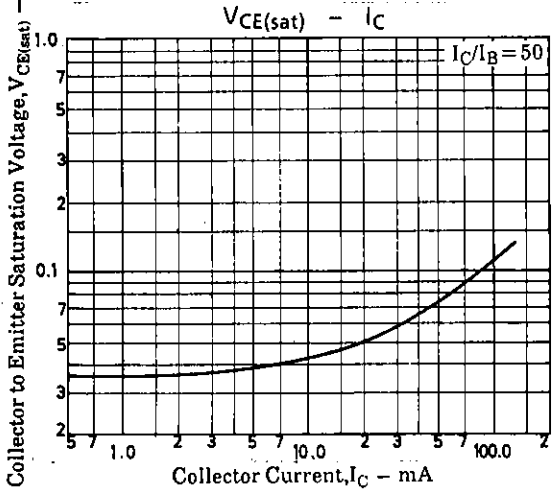
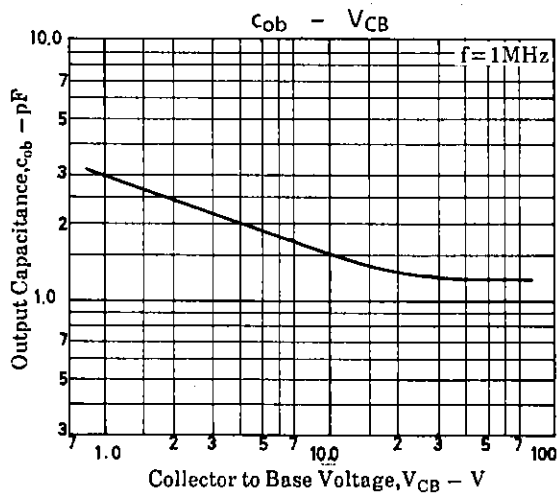
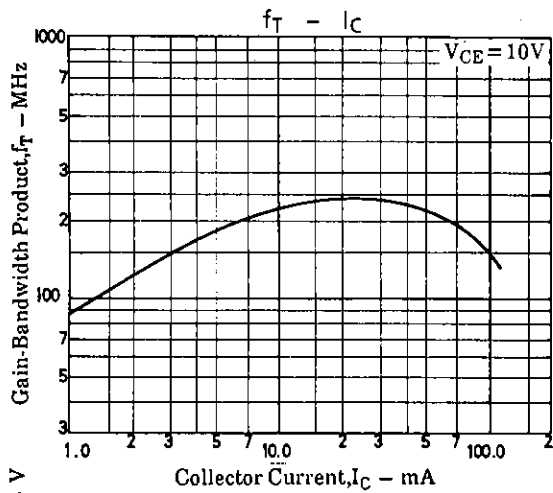
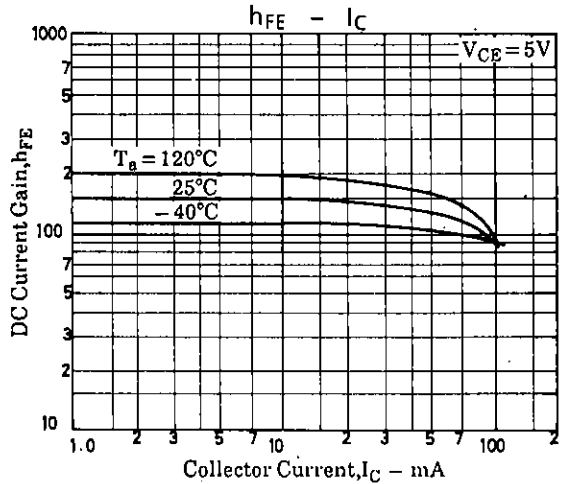
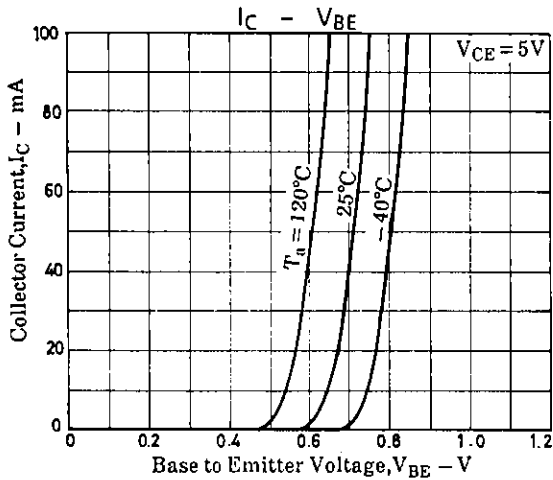
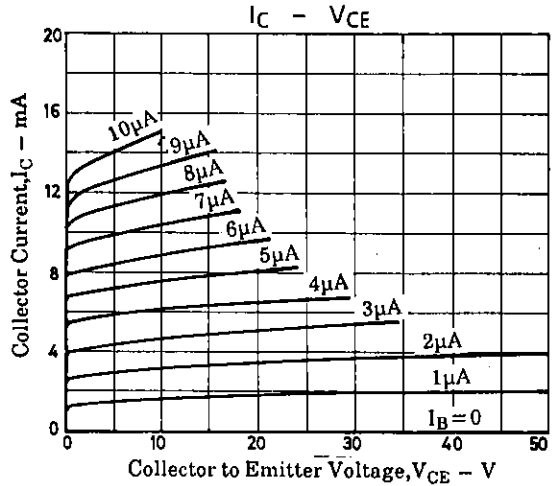
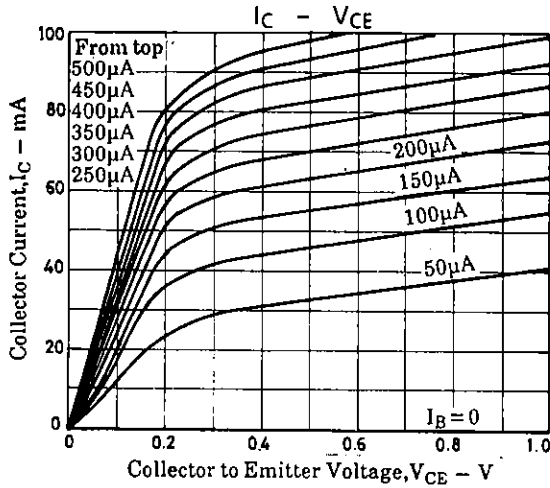


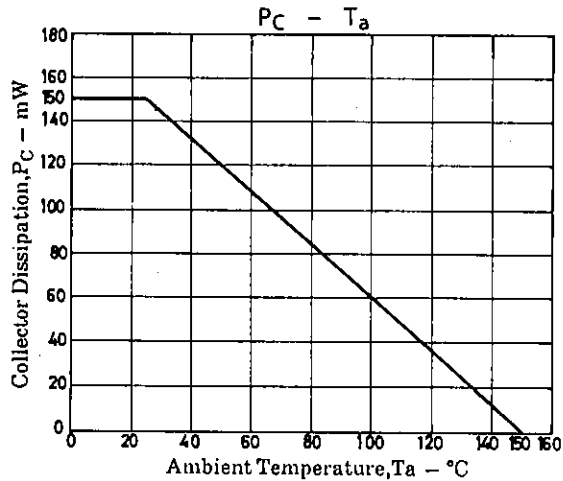
SANYO : MOP

B : Base
C : Collector
E : Emitter

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